

AMENDMENTS TO THE CLAIMS

Please cancel claims 6-12 and 17-22 without prejudice or disclaimer. A complete listing of all pending claims is shown below.

1. (Original) A semiconductor device comprising:
 - a semiconductor substrate;
 - a high-dielectric-constant film on the semiconductor substrate; and
 - a nitride layer on the high-dielectric-constant film.
2. (Original) The semiconductor device according to claim 1 further comprising a p-type impurity-contained layer on the nitride layer.
3. (Original) The semiconductor device according to claim 1 wherein the nitride layer is formed by introducing nitrogen into a top surface portion of the high-dielectric-constant film.
4. (Original) The semiconductor device according to claim 1 wherein the semiconductor substrate is a silicon substrate or a silicon layer.
5. (Original) The semiconductor device according to claim 2 wherein the p-type impurity-contained layer is a boron-contained silicon layer.
6. (Canceled)
7. (Canceled)
8. (Canceled)
9. (Canceled)

10. (Canceled)
11. (Canceled)
12. (Canceled)

13. (Original) A semiconductor device comprising:
A semiconductor substrate;
a gate insulating film on the semiconductor substrate; and
a gate electrode formed on the gate insulating film and including at least a p-type impurity-contained layer,
wherein the gate insulating film includes a high-dielectric-constant film and a nitride layer on the high-dielectric-constant film.

14. (Original) The semiconductor device according to claim 13 wherein the nitride layer is formed by introducing nitrogen into a top surface portion of the high-dielectric-constant film.

15. (Original) The semiconductor device according to claim 13 wherein the semiconductor substrate is a silicon substrate or a silicon layer.

16. (Original) The semiconductor device according to claim 13 wherein the p-type impurity-contained layer is a boron-contained silicon layer.

17. (Canceled)
18. (Canceled)

19. (Canceled)

20. (Canceled)

21. (Canceled)

22. (Canceled)